

Dual N-channel TrenchMOS logic level FET

Rev. 5 — 27 December 2011

Product data sheet

1. Product profile

1.1 General description

Dual logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Simple gate drive required due to low gate charge

1.3 Applications

- DC-to-DC convertors
- Lithium-ion battery applications

1.4 Quick reference data

 Suitable for high frequency applications due to fast switching characteristics

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- Notebook computers
- Portable equipment

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 150 °C	-	-	30	V
I _D	drain current	$T_{sp} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{\text{Figure 3}}; \text{[1]}$	-	-	10.4	А
P _{tot}	total power dissipation	T _{sp} = 25 °C; see <u>Figure 2</u>	-	-	3.57	W
Static cha	racteristics					
R_{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 8 A; T _j = 25 °C; see <u>Figure 9</u> ; see <u>Figure 10</u>	-	17	20	mΩ
Dynamic	characteristics					
Q _{GD}	gate-drain charge	$V_{GS} = 5 \text{ V}; I_D = 5 \text{ A}; V_{DS} = 15 \text{ V};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 11}}{1}$	-	3.9	-	nC

[1] Single device conducting.

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2. Pinning information

Table 2.	Pinning	information			
Pin	Symbol	Description	Simplified outline	Graphic symbol	
1	S1	source1			
2	G1	gate1			
3	S2	source2			
4	G2	gate2			
5	D2	drain2			
6	D2	drain2	SOT96-1 (SO8)	S1 G1 S2 G2	
7	D1	drain1		mbk725	
8	D1	drain			

3. Ordering information

Table 3. Ordering information				
Type number	Package			
	Name	Description	Version	
PHKD13N03LT	SO8	plastic small outline package; 8 leads; body width 3.9 mm	SOT96-1	

4. Limiting values

Table 4.Limiting values

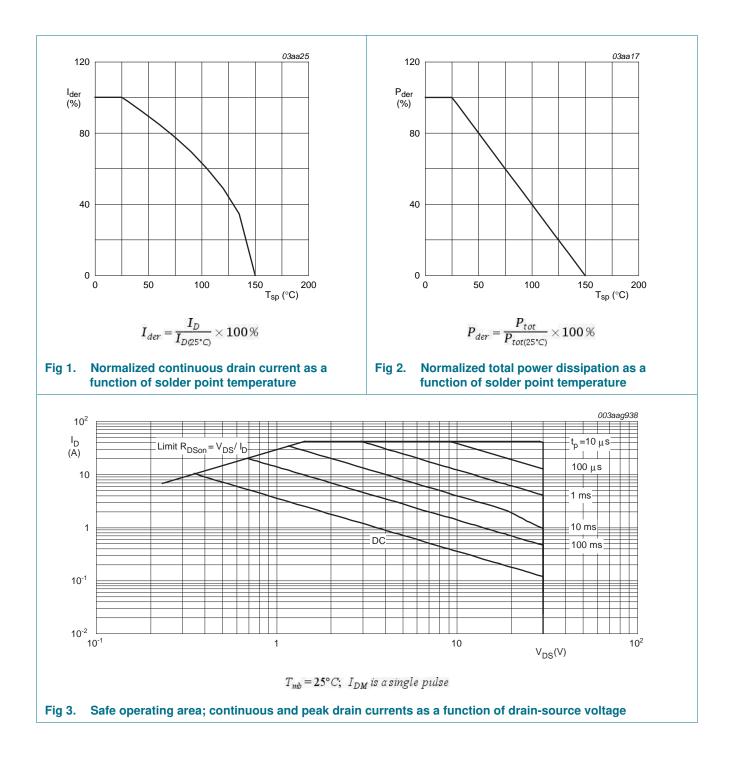
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 150 °C		-	30	V
V _{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 150 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	30	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	$T_{sp} = 100 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{10000000000000000000000000000000000$	[1]	-	6.6	А
		$T_{sp} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{\text{Figure 3}};$	[1]	-	10.4	А
I _{DM}	peak drain current	T_{sp} = 25 °C; pulsed; $t_p \le 10 \ \mu s$; see Figure 3	[1]	-	42	А
P _{tot}	total power dissipation	T _{sp} = 25 °C; see <u>Figure 2</u>		-	3.57	W
T _{stg}	storage temperature			-55	150	°C
Tj	junction temperature			-55	150	°C
Source-drai	in diode					
I _S	source current	T _{sp} = 25 °C	[1]	-	3.2	А
I _{SM}	peak source current	$T_{sp} = 25 \text{ °C}; \text{ pulsed}; t_p \le 10 \mu\text{s}$	[1]	-	42	А

[1] Single device conducting.

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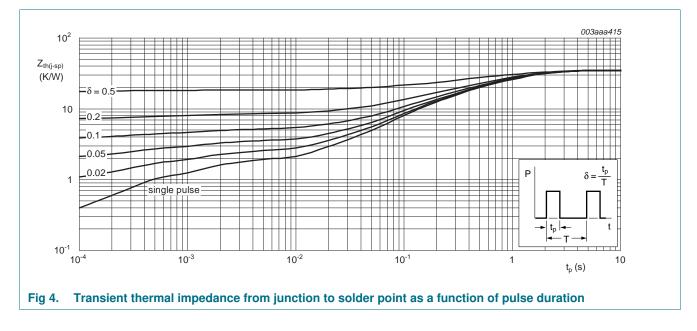
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Thermal characteristics 5.

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point	see Figure 4	-	-	35	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint ; mounted on a printed-circuit board	-	70	-	K/W



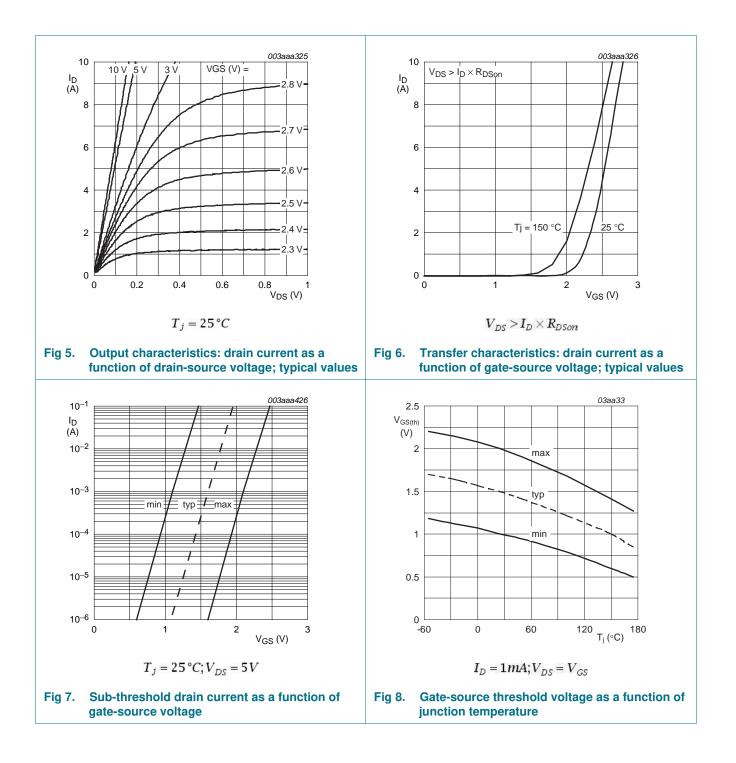
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6. Characteristics

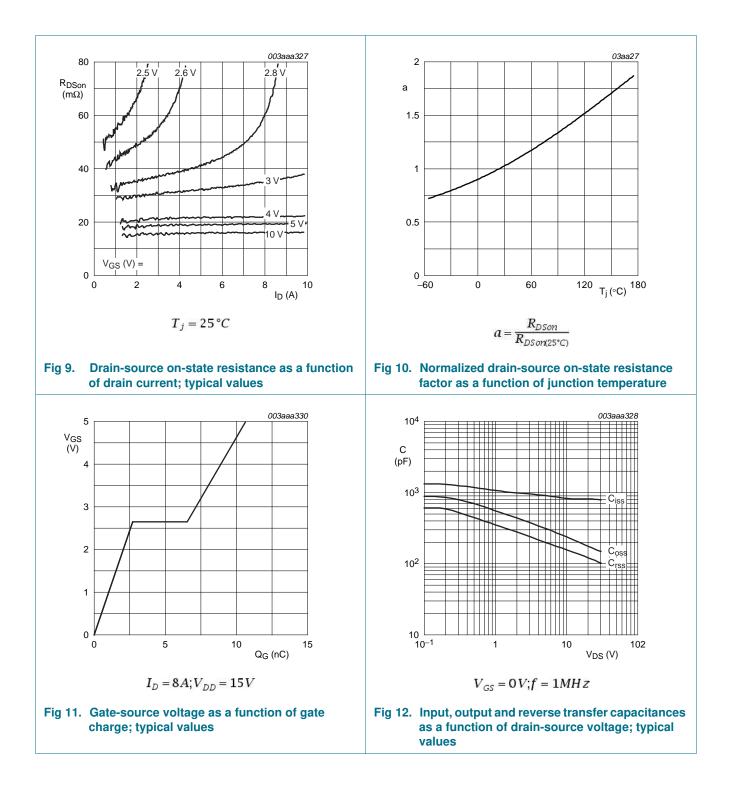
Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source breakdown	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ\text{C}$	27	-	-	V
	voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	30	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 250 \ \mu\text{A}; V_{DS} = V_{GS}; T_j = -55 \ ^\circ\text{C};$ see <u>Figure 8</u>	-	-	- 2.2	V
		$I_D = 250 \ \mu\text{A}; \ V_{DS} = V_{GS}; \ T_j = 150 \ ^\circ\text{C}; \ \text{see} \ \underline{Figure \ 8}$	0.5	-	-	V
		I_D = 250 µA; V_{DS} = V_{GS} ; T_j = 25 °C; see <u>Figure 8</u>	1	1.5	2	V
I _{DSS}	drain leakage current	$V_{DS} = 24 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μA
		$V_{DS} = 24 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 100 \text{ °C}$	-	-	5	μA
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
R _{DSon} drain-source on-state resistance		V _{GS} = 10 V; I _D = 8 A; T _j = 150 °C; see <u>Figure 9;</u> see <u>Figure 10</u>	-	-	34	mΩ
		V_{GS} = 4.5 V; I_D = 7 A; T_j = 25 °C; see Figure 9	- 21	21	26	mΩ
		V_{GS} = 10 V; I_D = 8 A; T_j = 25 °C; see <u>Figure 9</u> ; see <u>Figure 10</u>	-	17	20	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 5 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 5 \text{ V};$	-	10.7	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; see <u>Figure 11</u>	-	2.7	-	nC
Q _{GD}	gate-drain charge		-	3.9	-	nC
C _{iss}	input capacitance	$V_{DS} = 15 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	752	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 12</u>	-	200	-	pF
C _{rss}	reverse transfer capacitance		-	130	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 15 \ V; \ R_L = 10 \ \Omega; \ V_{GS} = 10 \ V;$	-	6	-	ns
t _r	rise time	$R_{G(ext)} = 6 \ \Omega; \ T_{j} = 25 \ ^{\circ}C; \ I_{D} = 1.5 \ A$	-	7	-	ns
t _{d(off)}	turn-off delay time		-	23	-	ns
t _f	fall time		-	11	-	ns
Source-d	rain diode					
V_{SD}	source-drain voltage	I _S = 7 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 13</u>	-	0.86	1.1	V
t _{rr}	reverse recovery time	$I_S = 7 \text{ A}; dI_S/dt = -100 \text{ A}/\mu\text{s}; \text{V}_{GS} = 0 \text{ V};$	-	25	-	ns
Q _r	recovered charge	V _{DS} = 30 V; T _j = 25 °C	-	5	-	nC

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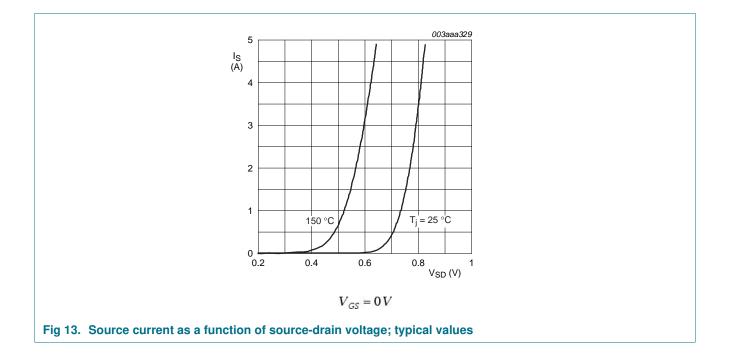
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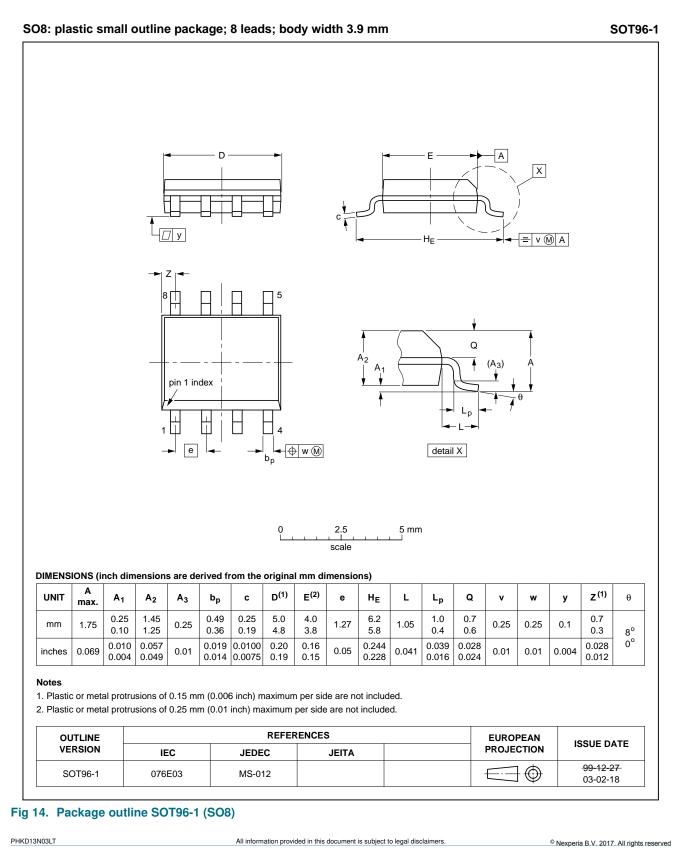


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7. Package outline



All information provided in

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8. Revision history

Table 7.Revision	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PHKD13N03LT v.5	20111227	Product data sheet	-	PHKD13N03LT v.4
Modifications:	 Various chang 	es to content.		
PHKD13N03LT v.4	20111122	Product data sheet	-	PHKD13N03LT v.3

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9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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